

Akshay M Arabhavi

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	InP/GaAsSb Double Heterojunction Bipolar Transistor Emitter-Fin Technology With $f_{MAX} = 1.2$ THz. IEEE Transactions on Electron Devices, 2022, 69, 2122-2129.	3.0	16
2	High-Speed Steep-Slope GaInAs Impact Ionization MOSFETs (I-MOS) With $SS = 1.25$ mV/decâ€”Part II: Dynamic Switching and RF Performance. IEEE Transactions on Electron Devices, 2022, 69, 3549-3556.	3.0	3
3	High-Speed Steep-Slope GaInAs Impact Ionization MOSFETs (I-MOS) With $SS = 1.25$ mV/decâ€”Part I: Material and Device Characterization, DC Performance, and Simulation. IEEE Transactions on Electron Devices, 2022, 69, 3542-3548.	3.0	2
4	Type-II GaInAsSb/InP Uniform Absorber High Speed Uni-Traveling Carrier Photodiodes. Journal of Lightwave Technology, 2021, 39, 2171-2176.	4.6	9
5	Performance prediction of InP/GaAsSb double heterojunction bipolar transistors for THz applications. Journal of Applied Physics, 2021, 130, .	2.5	5
6	Multiscale Compact Modelling of UTC-Photodiodes Enabling Monolithic Terahertz Communication Systems Design. Applied Sciences (Switzerland), 2021, 11, 11088.	2.5	1
7	Design of On-Wafer TRL Calibration Kit for InP Technologies Characterization up to 500 GHz. IEEE Transactions on Electron Devices, 2020, 67, 5441-5447.	3.0	6
8	InAs Channel Inset Effects on the DC, RF, and Noise Properties of InP pHEMTs. IEEE Transactions on Electron Devices, 2019, 66, 4685-4691.	3.0	10
9	Advances in InP/Ga(In)AsSb double heterojunction bipolar transistors (DHBTs). Japanese Journal of Applied Physics, 2019, 58, SB0802.	1.5	6
10	A Multiscale TCAD Approach for the Simulation of InP DHBTs and the Extraction of Their Transit Times. IEEE Transactions on Electron Devices, 2019, 66, 5084-5090.	3.0	12
11	Quaternary Graded-Base InP/GaInAsSb DHBTs With $f_{T} = 547$ GHz and $f_{MAX} = 547/784$ GHz. IEEE Electron Device Letters, 2018, 39, 1141-1144.	3.9	15
12	Scalable Compact Modeling of IIIâ€”V DHBTs: Prospective Figures of Merit Toward Terahertz Operation. IEEE Transactions on Electron Devices, 2018, 65, 5357-5364.	3.0	14